



STPS41H100CG/CT/CR

LOW DROP POWER SCHOTTKY RECTIFIER

MAIN PRODUCTS CHARACTERISTICS

$I_{F(AV)}$	2 x 20 A
V_{RRM}	100 V
T_j (max)	175 °C
V_F (max)	0.67 V

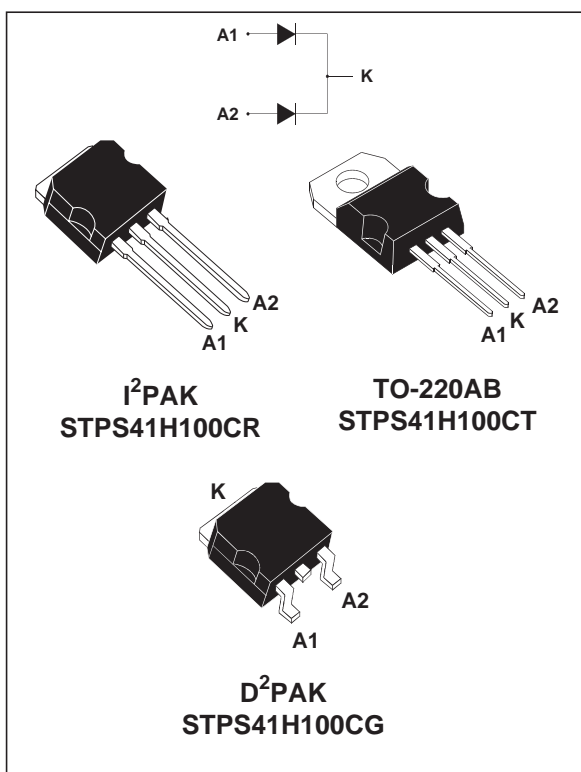
FEATURES AND BENEFITS

- NEGLIGIBLE SWITCHING LOSSES
- LOW LEAKAGE CURRENT
- GOOD TRADE OFF BETWEEN LEAKAGE CURRENT AND FORWARD VOLTAGE DROP
- LOW THERMAL RESISTANCE
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Dual center tab Schottky rectifier suited for Switch Mode Power Supply and high frequency DC to DC converters.

Packaged in D²PAK, I²PAK and TO-220AB, this device is intended for use in high frequency inverters.



ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		100	V
$I_{F(RMS)}$	RMS forward current		30	A
$I_{F(AV)}$	Average forward current	$T_c = 150^\circ\text{C}$ $\delta = 0.5$	Per diode 20	A
			Per device 40	
I_{FSM}	Surge non repetitive forward current	$t_p = 10$ ms sinusoidal	220	A
I_{RRM}	Peak repetitive reverse current	$t_p = 2$ μs square $F = 1$ kHz	1	A
P_{ARM}	Repetitive peak avalanche power	$t_p = 1$ μs $T_j = 25^\circ\text{C}$	18100	W
T_{stg}	Storage temperature range		- 65 to + 175	°C
T_j	Maximum operating junction temperature *		175	°C
dV/dt	Critical rate of rise reverse voltage		10000	V/ μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j-a)}$ thermal runaway condition for a diode on its own heatsink

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THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	1.5	$^{\circ}\text{C/W}$
		Total	0.8	
$R_{th(c)}$	Coupling		0.1	

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit	
I_R^*	Reverse leakage current	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$			10	μA	
		$T_j = 125^{\circ}\text{C}$			3	10	mA	
V_F^*	Forward voltage drop	$T_j = 25^{\circ}\text{C}$	$I_F = 20\text{ A}$			0.80	V	
		$T_j = 125^{\circ}\text{C}$		$I_F = 20\text{ A}$		0.62		0.67
		$T_j = 25^{\circ}\text{C}$		$I_F = 40\text{ A}$				0.90
		$T_j = 125^{\circ}\text{C}$			$I_F = 40\text{ A}$			0.70

Pulse test : * $t_p = 380\ \mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation :

$$P = 0.58 \times I_{F(AV)} + 0.0045 I_{F(RMS)}^2$$

Fig. 1: Conduction losses versus average current.

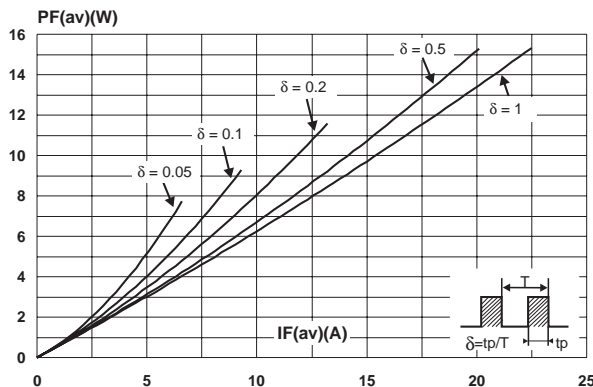


Fig. 2: Average forward current versus ambient temperature ($\delta = 0.5$).

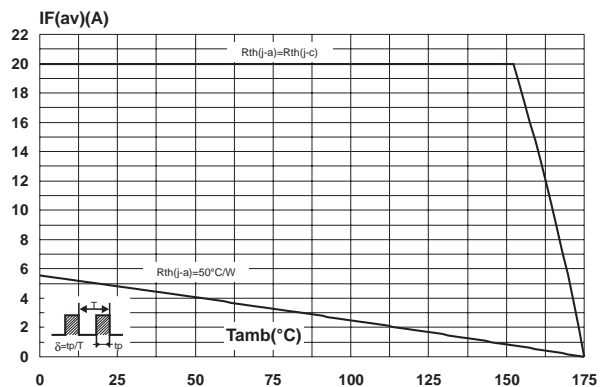


Fig. 3: Normalized avalanche power derating versus pulse duration.

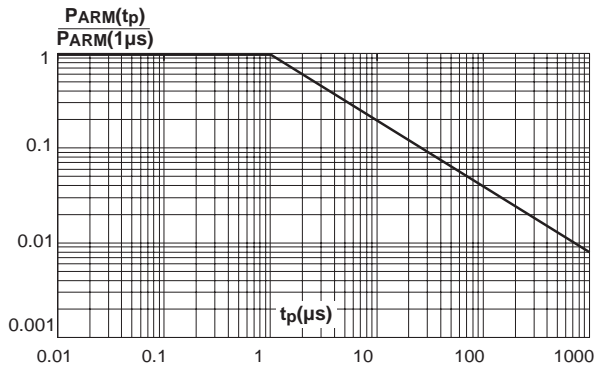


Fig. 4: Normalized avalanche power derating versus junction temperature.

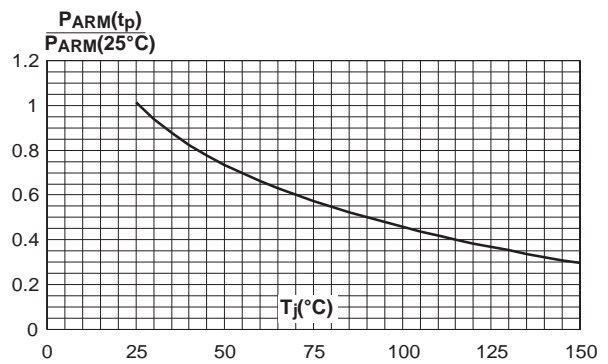


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values).

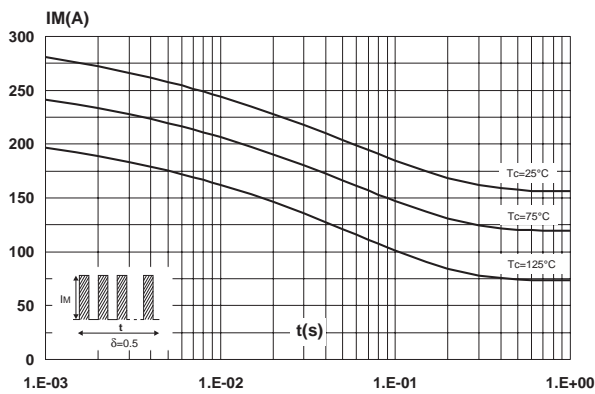


Fig. 6: Relative variation of thermal impedance junction to case versus pulse duration.

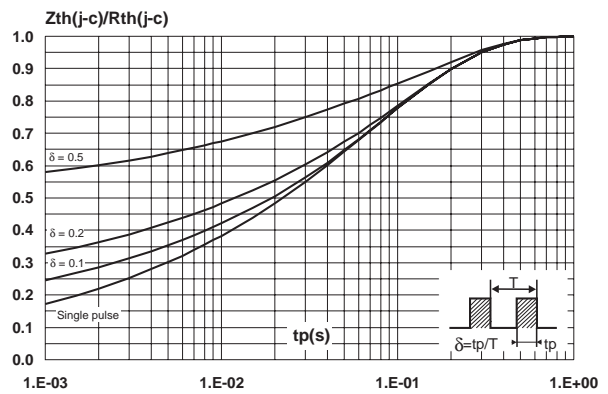


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values).

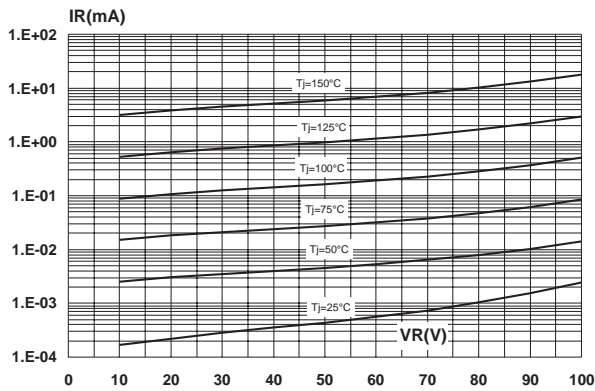


Fig. 8: Junction capacitance versus reverse voltage applied (typical values).

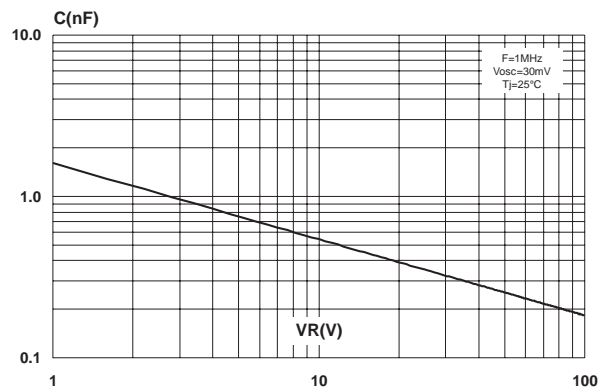


Fig. 9: Forward voltage drop versus forward current.

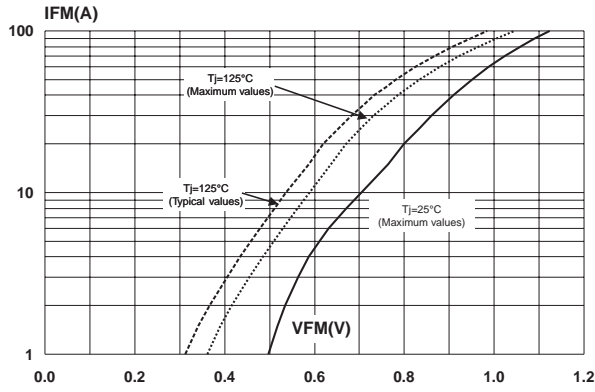
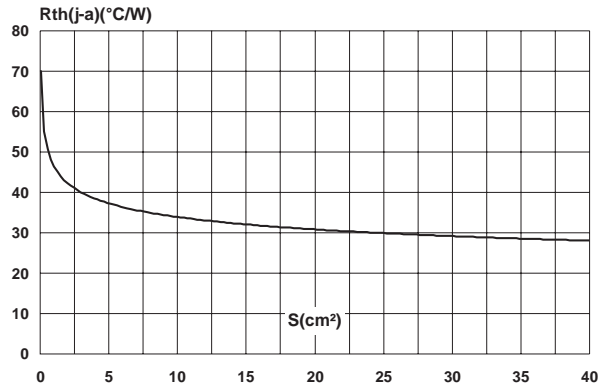
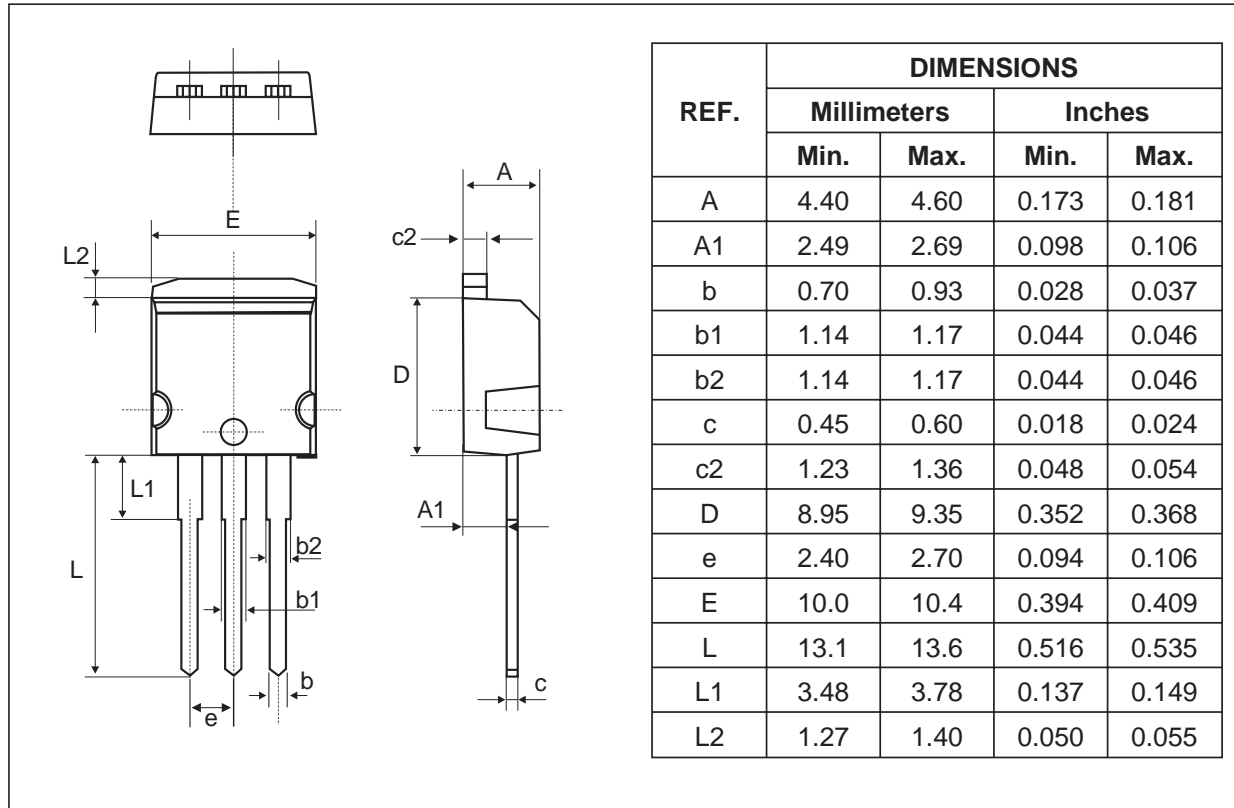


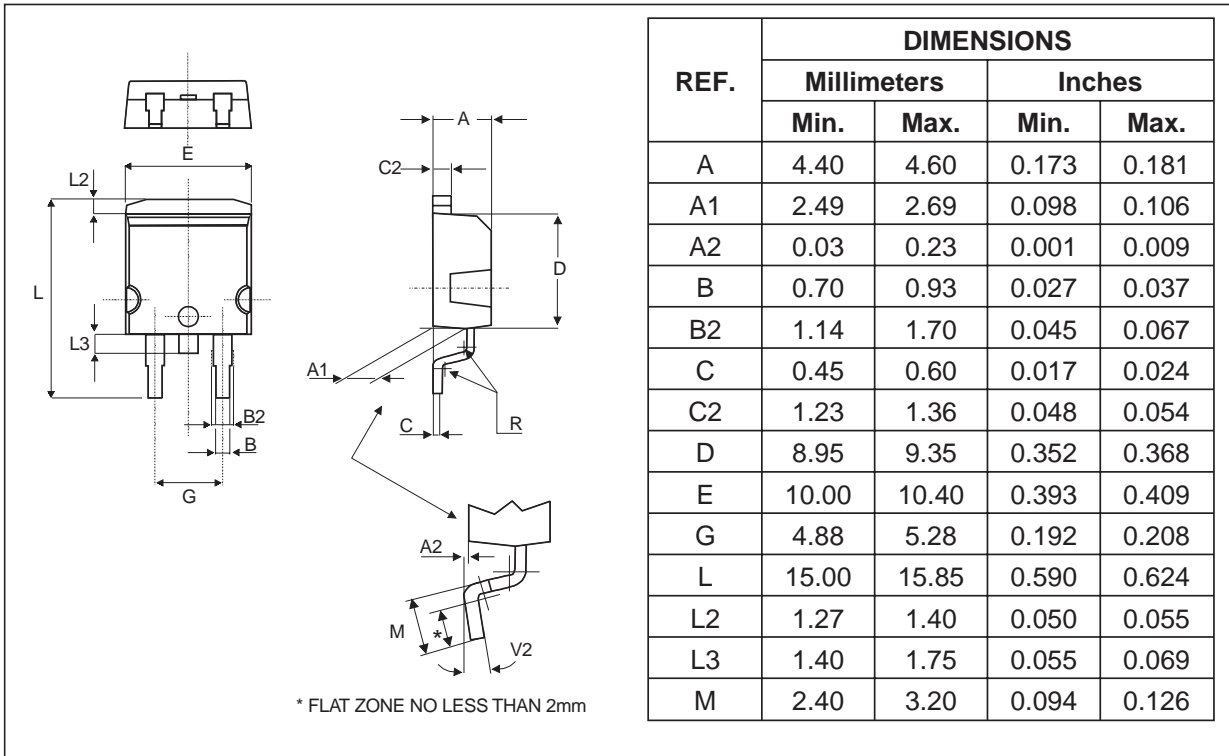
Fig. 10: Thermal resistance junction to ambient versus copper surface under tab (epoxy printed board FR4, Cu = 35µm). (STPS41H100CG only)



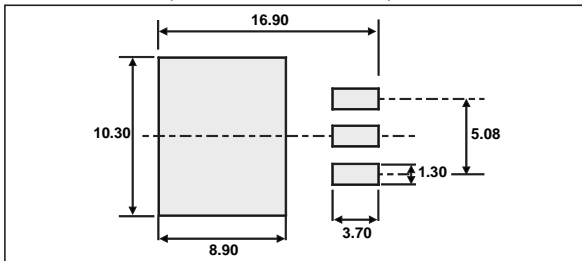
PACKAGE MECHANICAL DATA
I²PAK



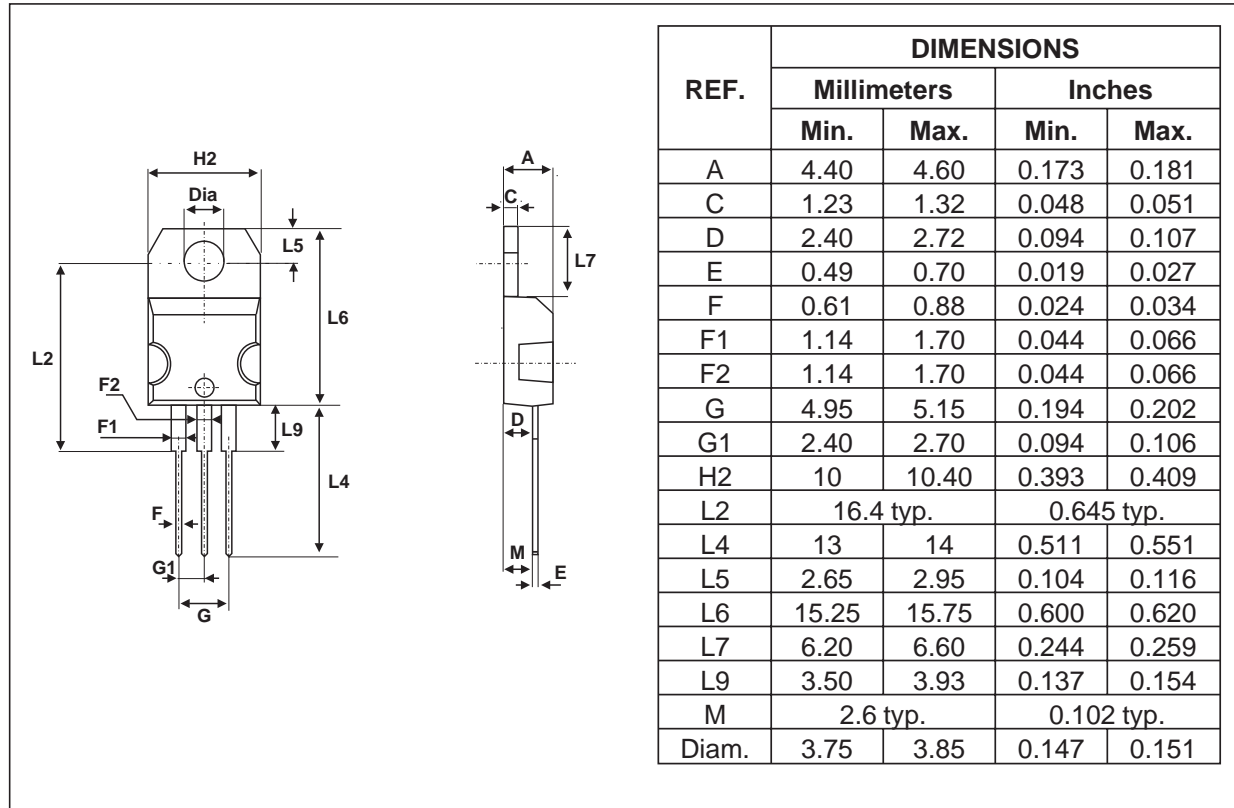
PACKAGE MECHANICAL DATA
D²PAK



FOOTPRINT (dimensions in mm)



PACKAGE MECHANICAL DATA
TO-220AB



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS41H100CT	STPS41H100CT	TO-220AB	2.20 g	50	Tube
STPS41H100CG	STPS41H100CG	D ² PAK	1.48 g	50	Tube
STPS41H100CG-TR	STPS41H100CG	D ² PAK	1.48 g	1000	Tape & reel
STPS41H100CR	STPS41H100CR	I ² PAK	1.49 g	50	Tube

■ EPOXY MEETS UL94,V0

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